

Title (en)
INSULATED GATE FIELD EFFECT TRANSISTORS

Title (de)
FELDEFFEKTTRANSISTOREN MIT ISOLIERTEM GATE

Title (fr)
TRANSISTORS A EFFET DE CHAMP A GRILLE ISOLEE

Publication
EP 1820217 A2 20070822 (EN)

Application
EP 05821637 A 20051201

Priority
• IB 2005053994 W 20051201
• GB 0426412 A 20041202

Abstract (en)
[origin: WO2006059300A2] A vertical power MOSFET includes active cells 8 and inactive cells 10. The active cells 8 are surrounded by inactive cells 10 on the surface of the substrate, and are fewer in number. The MOSFET may have a lower zero temperature coefficient current than cells in which all cells are active.

IPC 8 full level
H01L 29/00 (2006.01); **H01L 29/06** (2006.01); **H01L 29/08** (2006.01); **H01L 29/10** (2006.01); **H01L 29/78** (2006.01); **H01L 29/788** (2006.01)

CPC (source: EP KR US)
H01L 21/18 (2013.01 - KR); **H01L 29/0696** (2013.01 - EP); **H01L 29/0865** (2013.01 - EP); **H01L 29/1095** (2013.01 - EP);
H01L 29/7811 (2013.01 - EP US); **H01L 29/7813** (2013.01 - EP US); **H01L 29/7827** (2013.01 - EP); **H01L 29/788** (2013.01 - EP);
H01L 29/7828 (2013.01 - EP)

Citation (search report)
See references of WO 2006059300A2

Designated contracting state (EPC)
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC NL PL PT RO SE SI SK TR

Designated extension state (EPC)
AL BA HR MK YU

DOCDB simple family (publication)
WO 2006059300 A2 20060608; **WO 2006059300 A3 20080703**; CN 101288178 A 20081015; EP 1820217 A2 20070822;
GB 0426412 D0 20050105; JP 2008523586 A 20080703; KR 20070084612 A 20070824

DOCDB simple family (application)
IB 2005053994 W 20051201; CN 200580041244 A 20051201; EP 05821637 A 20051201; GB 0426412 A 20041202; JP 2007543983 A 20051201;
KR 20077012285 A 20070531